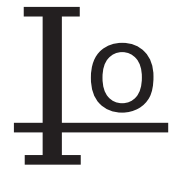


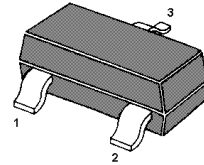
# MMBT8550

PNP Silicon Epitaxial Planar Transistor



for switching and amplifier applications.

As complementary type the NPN transistor MMBT8050 is recommended.



1.BASE 2.EMITTER 3.COLLECTOR  
SOT-23 Plastic Package

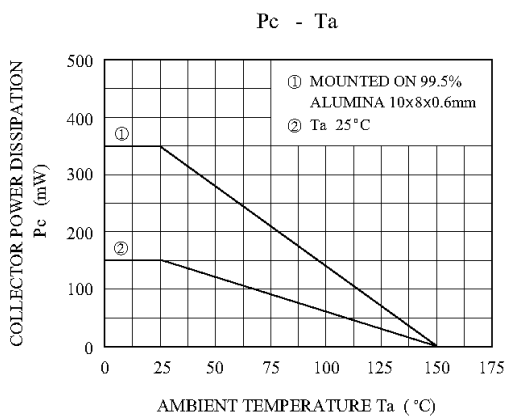
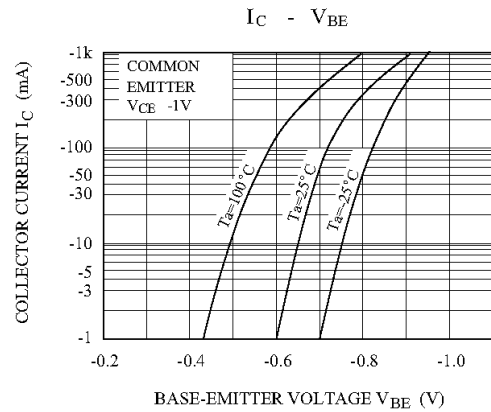
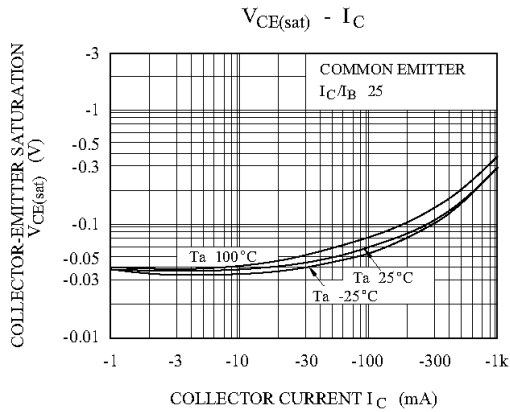
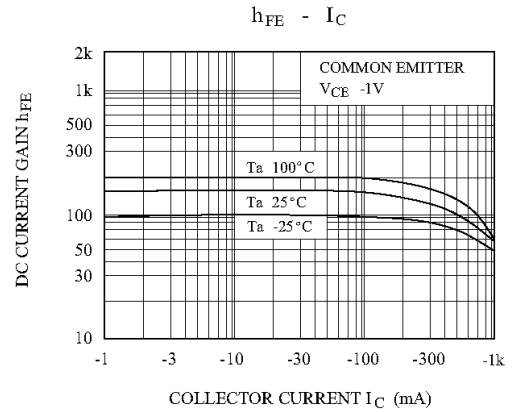
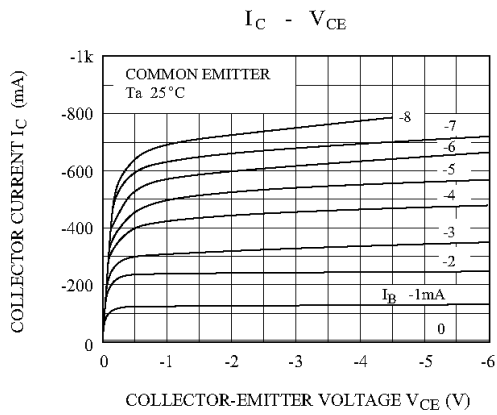
## Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	25	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	600	mA
Power Dissipation	$P_{tot}$	350	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_s$	- 55 to + 150	$^\circ\text{C}$

## Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE} = 1\text{ V}$ , $-I_C = 100\text{ mA}$	MMBT8550C	$h_{FE}$	100	-	250	-
	MMBT8550D	$h_{FE}$	160	-	400	-
		$h_{FE}$	40	-	-	-
Collector Base Cutoff Current at $-V_{CB} = 35\text{ V}$	$-I_{CBO}$	-	-	100	nA	
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	40	-	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 2\text{ mA}$	$-V_{(BR)CEO}$	25	-	-	V	
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	-	-	V	
Collector Emitter Saturation Voltage at $-I_C = 500\text{ mA}$ , $-I_B = 50\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V	
Base Emitter Saturation Voltage at $-I_C = 500\text{ mA}$ , $-I_B = 50\text{ mA}$	$-V_{BE(sat)}$	-	-	1.2	V	
Gain Bandwidth Product at $-V_{CE} = 5\text{ V}$ , $-I_C = 10\text{ mA}$	$f_T$	-	100	-	MHz	

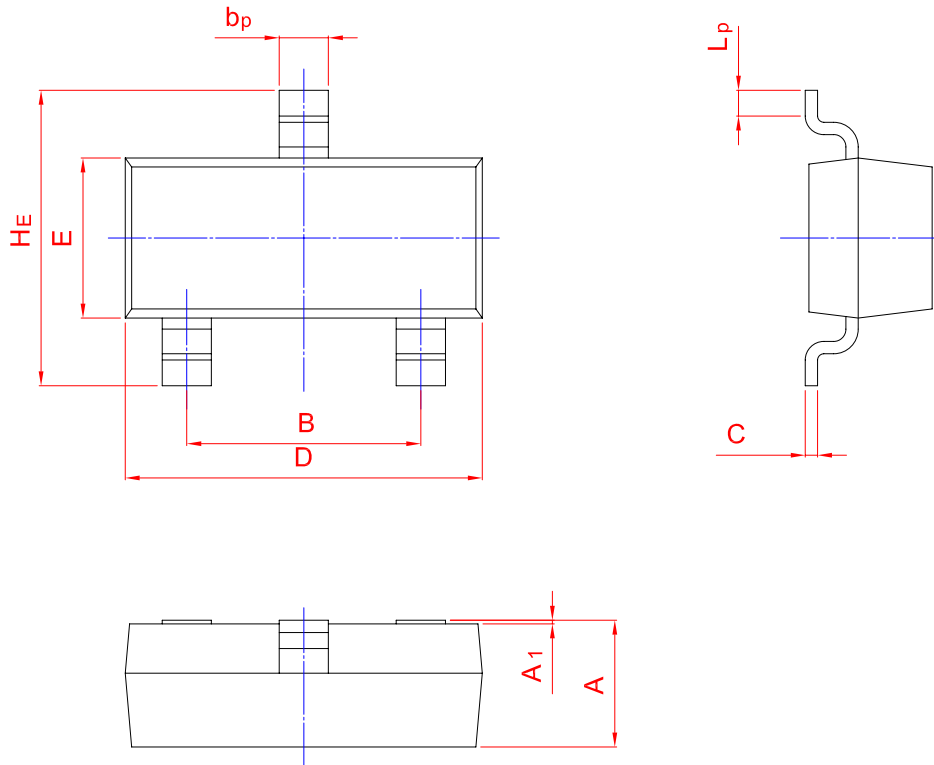
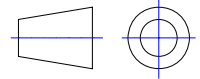
# MMBT8550



# PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b <sub>p</sub>	C	D	E	H <sub>E</sub>	A <sub>1</sub>	L <sub>p</sub>
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20